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Hyperfast Rectifier, 15 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES

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3D M	odels



PRIMARY CHARACTERISTICS								
I _{F(AV)}	15 A							
V _R	1200 V							
V _F at I _F at 125 °C	2.1 V							
t _{rr}	29 ns							
T _J max.	175 °C							
Package	TO-220AC 2L							
Circuit configuration	Single							

FEATURES

- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant. Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Repetitive peak reverse voltage	V _{RRM}		1200	V					
Average rectified forward current	I _{F(AV)}	T _C = 98 °C, D = 0.50	15						
Repetitive peak forward current	I _{FRM}	T _C = 98 °C, D = 0.50, f = 20 kHz	30	А					
Non-repetitive peak surge current	I _{FSM}	$T_C = 45 \text{ °C}, t_p = 10 \text{ ms}, \text{ sine wave}$	110						
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	(MBOL TEST CONDITIONS MIN. TYP.				UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-				
Forward voltage	V _F	I _F = 15 A	-	2.5	3.3	V			
		I _F = 15 A, T _J = 125 °C	-	2.1	-				
Reverse leakage current	I _R	$V_{R} = V_{R}$ rated	-	-	50	μA			
neverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μΑ			
Junction capacitance	CT	V _R = 200 V	-	10	-	pF			
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH			

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 For technical questions within your region: DiodesAsia@vishay.com, DiodesEurope@vishay.com

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ROHS COMPLIANT HALOGEN



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST	CONDITIONS	MIN.	TYP.	MAX.	UNITS			
		T _J = 25 °C	1 A, 30 V, 100 A/µs	-	29	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	96	-	ns			
		T _J = 125 °C		-	137	-				
Peak recovery current	1	T _J = 25 °C	l _F = 10 A dl _F /dt = 600 A/μs	-	11.5	-	A			
	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	16	-				
Davience in a construction of a construction	Q _{rr}	T _J = 25 °C		-	375	-	nC			
Reverse recovery charge		T _J = 125 °C		-	900	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	77.5	-	ns			
neverse recovery time		T _J = 125 °C	$I_{\rm F} = 15 {\rm A}$	-	106	-	115			
Pook receivery ourrent	I _{RRM}	T _J = 25 °C		-	21	-	A			
Peak recovery current		T _J = 125 °C	dl _F /dt = 1000 A/µs V _B = 800 V	-	29	-				
Davience management also man	_	T _J = 25 °C		-	680	-				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1600	-	ПС			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7	°C/W			
Weight			-	2.0	-	g			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Marking device		Case style TO-220AC 2L	E5TX1512TH						

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VS-E5TX1512THN3

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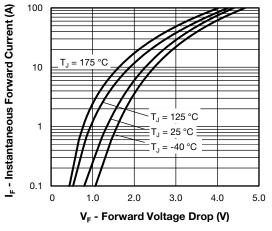


Fig. 1 - Forward Voltage Drop Characteristics

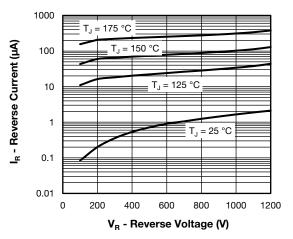


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

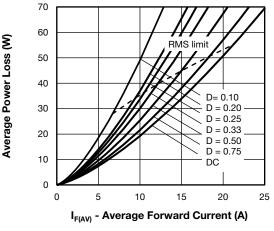


Fig. 5 - Forward Power Loss Characteristics

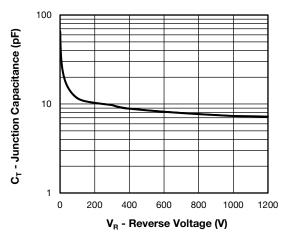


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

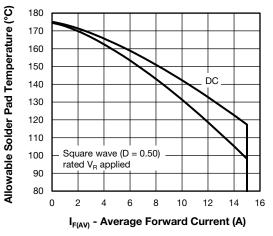


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

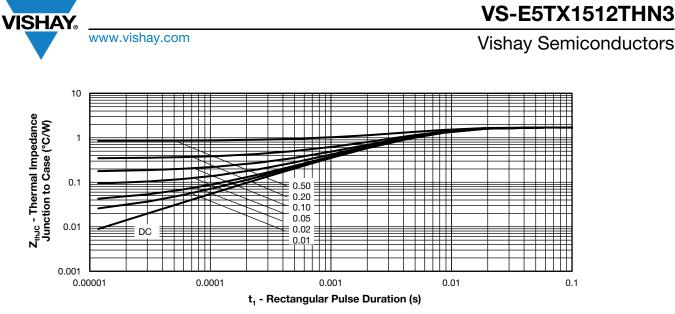


Fig. 6 - Transient Thermal Impedance, Junction to Case

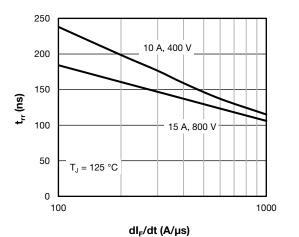


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

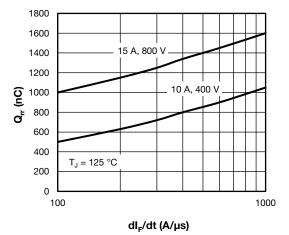


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt

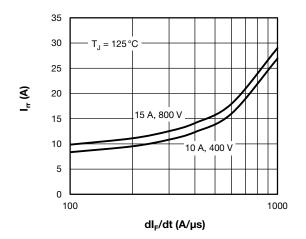


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt



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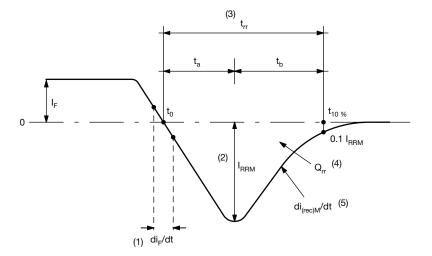


Fig. 10 - Reverse Recovery Waveform and Definitions

- Notes
- ⁽¹⁾ di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM} (4) Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

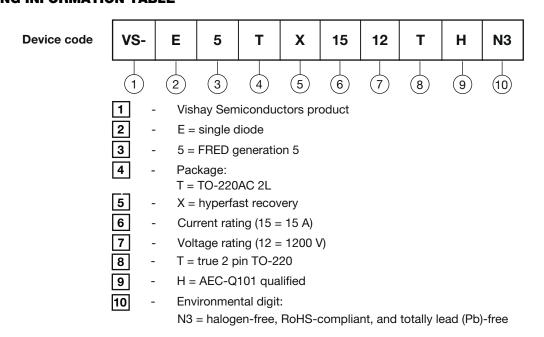
 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

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ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-E5TX1512THN3	50	1000	Antistatic plastic tube					

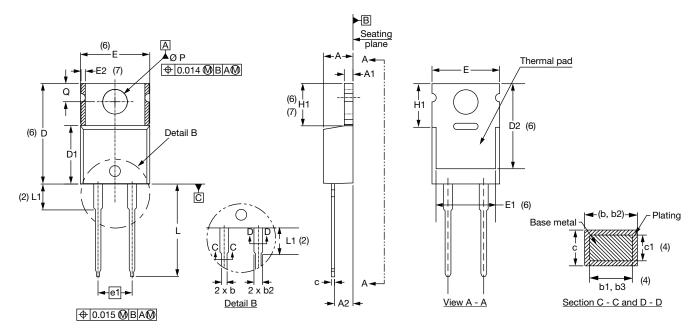
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96069				
Part marking information	www.vishay.com/doc?95391				
SPICE Model	www.vishay.com/doc?97160				



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TO-220AC 2L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040			H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4		L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068			L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4		ØΡ	3.54	3.73	0.139	0.147	
с	0.36	0.61	0.014	0.024			Q	2.60	3.00	0.102	0.118	
c1	0.36	0.56	0.014	0.022	4							
D	14.85	15.25	0.585	0.600	3							
D1	8.38	9.02	0.330	0.355								
D2	11.68	12.88	0.460	0.507	6							
E	10.11	10.51	0.398	0.414	3, 6							

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

⁽⁵⁾ Controlling dimension: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

⁽⁸⁾ Outline conforms to JEDEC[®] TO-220, except D2, where JEDEC[®] minimum is 0.480"

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